

BCM65S04D3

Silicon Carbide Schottky Diode

650V, 4A



bestirpower

Description

BCM65S04D3 utilizes Bestirpower's advanced silicon carbide diode technology. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the family is suitable for application requiring high power efficiency.

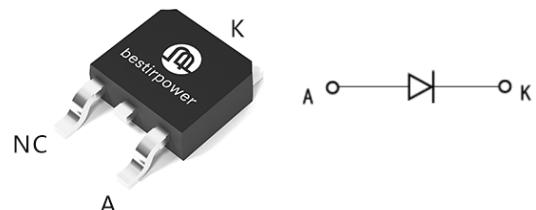
Benefits

- High frequency
- Low heat dissipation requirements
- Reduce size and cost of the system
- Reduced EMI
- High-reliability

Features

V _{RRM}	I _F	T _C	Q _c
650 V	4 A	162 °C	9.5 nC

- Benchmark switching behavior
- No reverse recovery
- Positive Temperature Coefficient
- Easy to paralleling
- RoHS compliant / Halogen-free



Applications

- Power factor correction
- Solar inverter
- Data Center
- Uninterruptible power supply



Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{RRM}	Repetitive Peak Reverse Voltage	650	V	
I _F	Forward Current	T _C = 25°C	15	A
		T _C = 135°C	7	A
		T _C = 162°C	4	A
I _{F,SM}	Non-Repetitive Forward Surge Current	T _C = 25°C, t _p = 10 ms	42	A
		T _C = 110°C, t _p = 10 ms	33	A
I _{F,RM}	Repetitive Peak Forward Surge Current	T _C = 25°C, t _p = 10 ms	37	A
I ² dt value	J I ² t	T _C = 25°C, t _p = 10 ms	8	A ² s
		T _C = 110°C, t _p = 10 ms	5	A ² s
P _{tot}	Power Dissipation	T _C = 25°C	84	W
		T _C = 110°C	37	W
		T _C = 150°C	14	W
T _{J,T_{STG}}	Operating Junction and Storage Temperature	-55 to +175	°C	

Thermal Characteristics

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Typ.	1.77	°C/W

Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{DC}	DC blocking voltage		650			V
V _F	Forward Voltage	I _F =4A, T _J =25°C	-	1.35	1.7	V
		I _F =4A, T _J =175°C	-	1.7	1.9	
I _R	Reverse Current	V _R = 650 V, T _J = 25°C	-	1	20	μA
		V _R = 650 V, T _J = 175°C	-	12	100	
Q _C	Total Capacitive Charge	V _R = 400 V, T _J = 25°C	-	9.5	-	nC
C	Total Capacitance	V _R = 0 V, f = 1MHz	-	185	-	pF
		V _R = 200 V, f = 1MHz	-	19	-	
		V _R = 400 V, f = 1MHz	-	16.7	-	
E _C	Capacitance Stored Energy	V _R = 400 V, T _C = 25°C	-	2.4	-	μJ

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
BCM65S04D3	BCM65S04D3	TO252NC	Tape & Reel	330 mm	16 mm	2500 units

Typical Performance Characteristics

Figure 1. Forward Characteristics

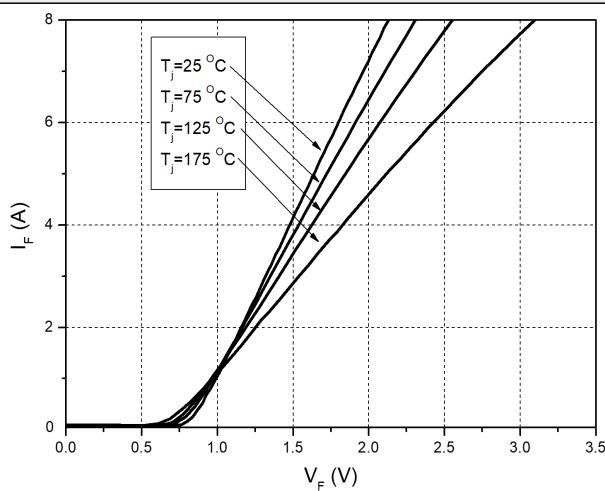


Figure 2. Reverse Characteristics

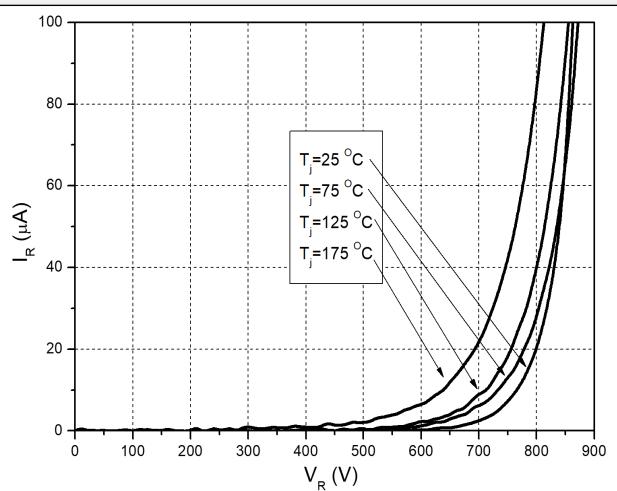


Figure 3. Peak Forward Current Derating

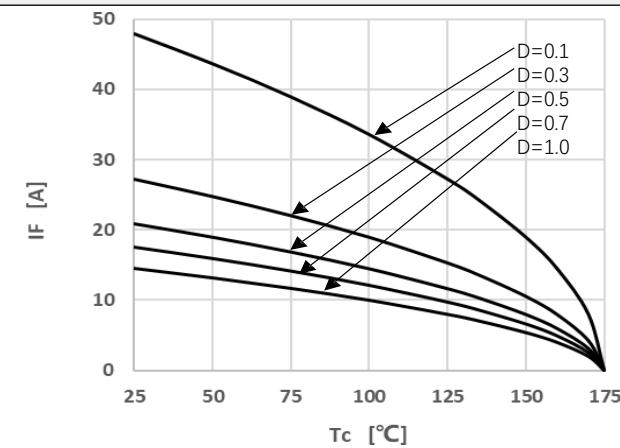


Figure 4. Power Dissipation

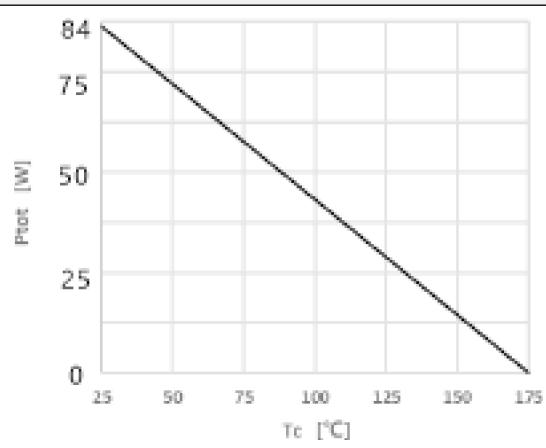


Figure 5. Capacitance vs. Reverse Voltage

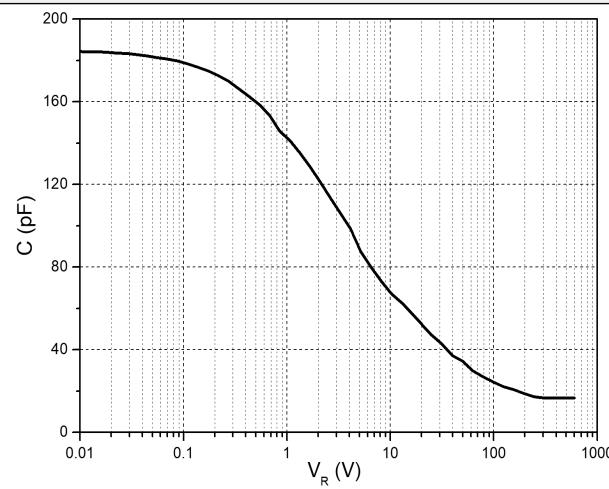
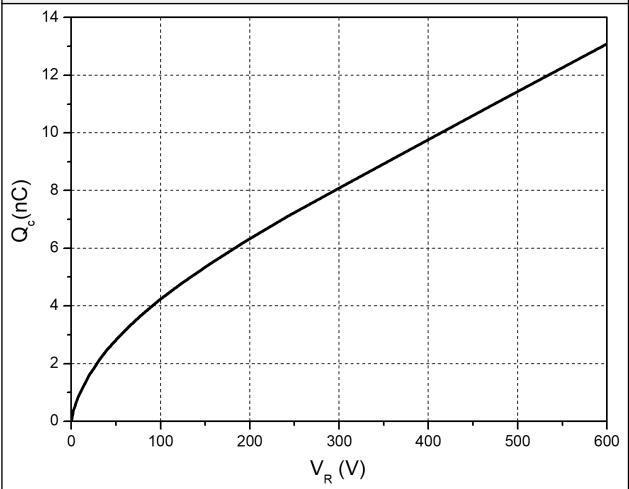
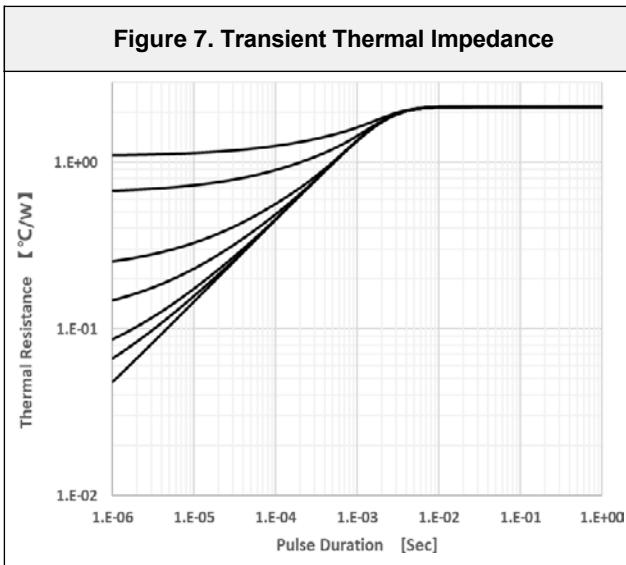


Figure 6. Capacitance Charge vs. Reverse Voltage

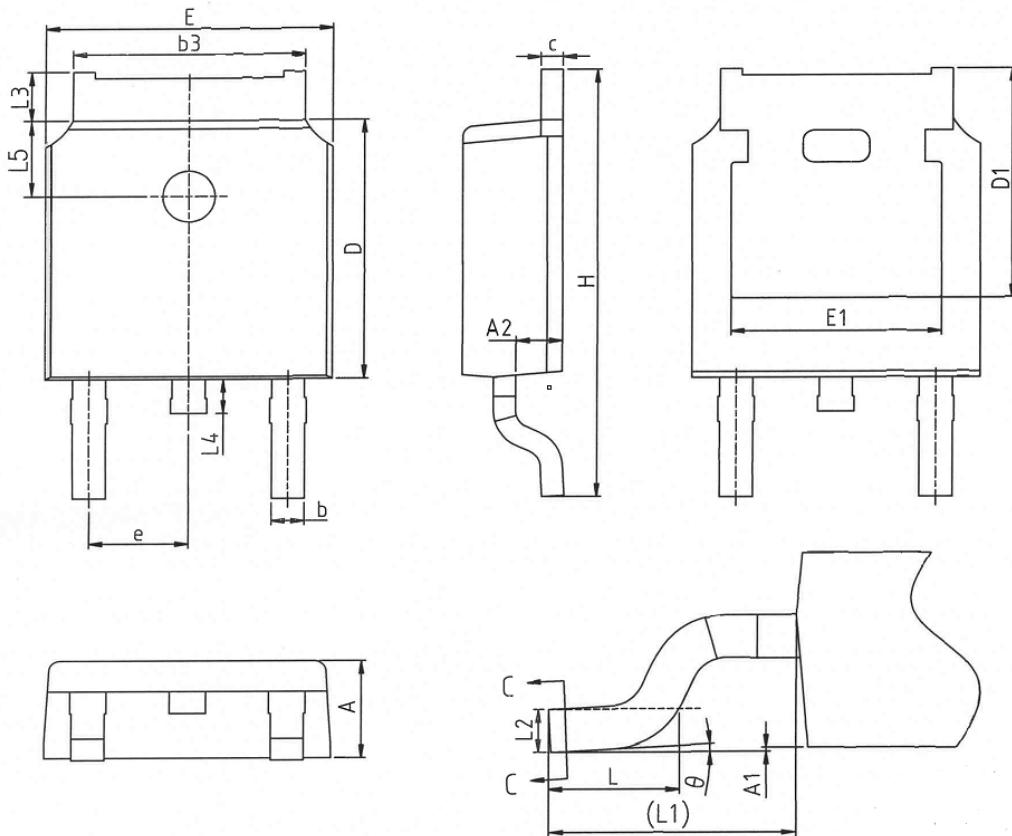


Typical Performance Characteristics



Package Outlines

TO252NC



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.12
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
theta	0°	-	8°

* Dimensions in millimeters

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